



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

SUPPLEMENTAL PRELIMINARY AMENDMENT

January 20, 2000

Prior to examination, please amend the above-identified application as follows:

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Please add the following new claims:

B1

- (a) forming a MISFET on main surface of a semiconductor substrate,
- (b) forming a first insulating film over the MISFET,
- (c) forming a first conductor film on the first insulating film,
- (d) forming a second insulating film over the first conductor film,
- (e) forming a first electrode for a capacitor cell on the second insulating film,